

TSM4936D

30V N-Channel MOSFET



SOP-8

Pin Definition:



1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2

4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)		
30	36 @ V _{GS} = 10V	5.9		
	53 @ V _{GS} = 4.5V	4.9		

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

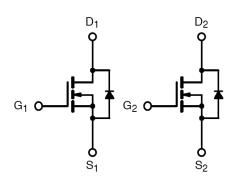
Application

- High-Side DC/DC Conversion
- Notebook
- Sever

Ordering Information

Part No.	Package	Packing
TSM4936DCS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	5.9	Α	
Pulsed Drain Current		I _{DM}	40	Α	
Continuous Source Current (Diode Con	nduction) ^{a,b}	I _S	1.0	Α	
Maximum Power Dissipation	Ta = 25°C	В	3.0	W	
	Ta = 75°C	P _D	2.1		
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JF}$	32	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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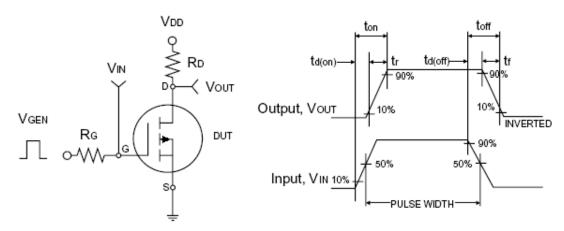


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	30	-		V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.4	3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}		-	±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I _{DSS}		1	1.0	μΑ
On-State Drain Current ^a	V _{DS} ≥ 5V, V _{GS} = 10V	I _{D(ON)}	30			Α
Dunin Course On Otata Basistanas	$V_{GS} = 10V, I_D = 5.9A$			32	36	mΩ
Drain-Source On-State Resistance ^a	$V_{GS} = 4.5V, I_D = 4.9A$	R _{DS(ON)}		42	53	
Forward Transconductance ^a	V _{DS} = 15V, I _D = 5.9A	g _{fs}		15		S
Diode Forward Voltage	I _S = 1A, V _{GS} = 0V	V_{SD}		0.76	1.0	V
Dynamic ^b						
Total Gate Charge	\/ - 15\/ - 5 0 0	Q_g		13		
Gate-Source Charge	$V_{DS} = 15V, I_D = 5.9A,$	Q_{gs}		4.2		nC
Gate-Drain Charge	V _{GS} = 10V	Q_{gd}		3.1		
Input Capacitance	\/ - 45\/ \/ - 0\/	C _{iss}		610		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		100		pF
Reverse Transfer Capacitance	1 = 1.0WIDZ	C _{rss}		77		
Switching ^c						
Turn-On Delay Time	V - 45V D - 450	t _{d(on)}		9.1		
Turn-On Rise Time	$V_{DD} = 15V, R_L = 15\Omega,$	t _r		16.5		nC
Turn-Off Delay Time	$I_D = 1A$, $V_{GEN} = 10V$,	t _{d(off)}		23		nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		3.5		

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

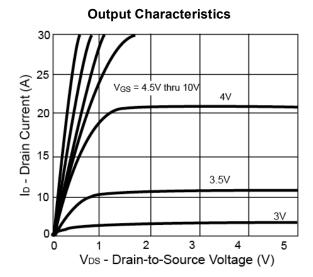




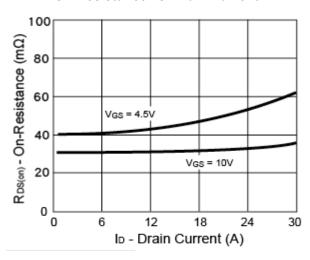


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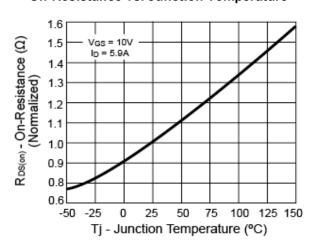
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



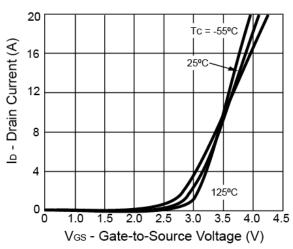
On-Resistance vs. Drain Current



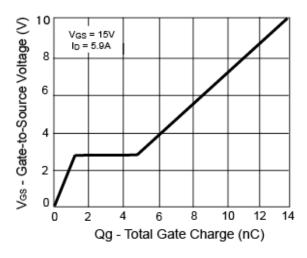
On-Resistance vs. Junction Temperature



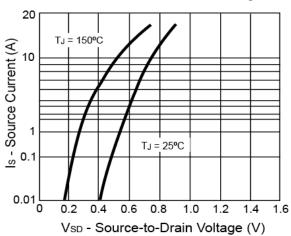
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





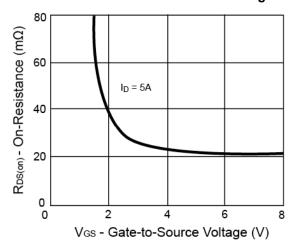






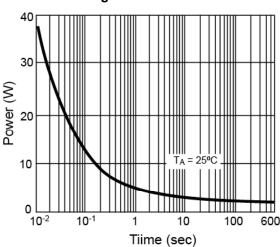
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

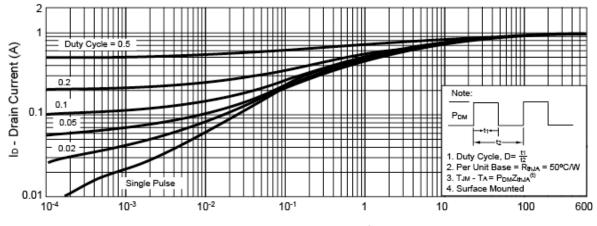


Threshold Voltage 0.2 0.1 V_{GS(th)} - Variance (V) ID = 1mA -0.0 -0.1 -0.2 -0.3 -0.4 -25 25 100 125 150 -50 0 50 75 Tj - Junction Temperature (°C)

Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

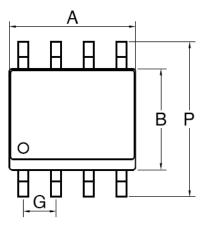


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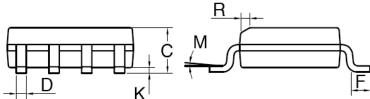
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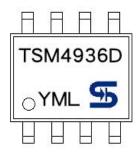
SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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